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IGBT

SGP40N60UF

Ultra-Fast IGBT

General Description

Fairchild's UF series of Insulated Gate Bipolar Transistors (IGBTs) provides low conduction and switching losses. The UF series is designed for applications such as motor control and general inverters where high speed switching is a required feature.

Features

- · High speed switching
- Low saturation voltage : $V_{CE(sat)} = 2.1 \text{ V } @ I_C = 20 \text{A}$
- High input impedance

Applications

AC & DC motor controls, general purpose inverters, robotics, and servo controls.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description		SGP40N60UF	Units
V _{CES}	Collector-Emitter Voltage		600	V
V _{GES}	Gate-Emitter Voltage		± 20	V
	Collector Current	@ T _C = 25°C	40	А
I _C	Collector Current	@ T _C = 100°C	20	Α
I _{CM (1)}	Pulsed Collector Current		160	Α
P _D	Maximum Power Dissipation	@ T _C = 25°C	160	W
	Maximum Power Dissipation	@ T _C = 100°C	64	W
TJ	Operating Junction Temperature		-55 to +150	°C
T _{stg}	Storage Temperature Range		-55 to +150	°C
TL	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seco	onds	300	°C

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		0.77	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		62.5	°C/W

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Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Cha	racteristics					
BV _{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_{C} = 250uA$	600			V
$\Delta B_{VCES}/$ ΔT_J	Temperature Coefficient of Breakdown Voltage	V _{GE} = 0V, I _C = 1mA		0.6		V/°C
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$			250	uA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$			± 100	nA
On Chai	racteristics					
V _{GE(th)}	G-E Threshold Voltage	$I_C = 20$ mA, $V_{CE} = V_{GE}$	3.5	4.5	6.5	V
	Collector to Emitter	$I_C = 20A$, $V_{GE} = 15V$		2.1	2.6	V
$V_{CE(sat)}$	Saturation Voltage	$I_C = 40A$, $V_{GE} = 15V$		2.6		V
	c Characteristics	I				
C _{ies}	Input Capacitance	$V_{CE} = 30V_{V_{GE}} = 0V_{V_{CE}}$		1430		pF
C _{oes}	Output Capacitance	f = 1MHz		170		pF
C _{res}	Reverse Transfer Capacitance			50		pF
	ng Characteristics			30		pi
Switchir	ng Characteristics Turn-On Delay Time			15		ns
Switchir	ng Characteristics Turn-On Delay Time Rise Time					
Switchir t _{d(on)} t _r	ng Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time	V _{CC} = 300 V, I _C = 20A,		15 30 65	 130	ns
Switching $t_{d(on)}$ t_r $t_{d(off)}$ t_f	ng Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time	$R_G = 10\Omega, V_{GE} = 15V,$		15 30 65 50		ns ns
Switching t _{d(on)} t _r t _{d(off)} t _f	Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss			15 30 65	 130	ns ns ns
Switchin t _{d(on)} t _r t _{d(off)} t _f E _{on}	ng Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time	$R_G = 10\Omega, V_{GE} = 15V,$		15 30 65 50	 130 150	ns ns ns
Switchir	Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss	$R_G = 10\Omega, V_{GE} = 15V,$	 	15 30 65 50 160	 130 150	ns ns ns ns
Switchin td(on) tr td(off) tf Eon Ets	Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss	$R_G = 10\Omega, V_{GE} = 15V,$	 	15 30 65 50 160 200	 130 150 	ns ns ns ns uJ
Switchin t _{d(on)} t _r t _{d(off)} t _f E _{on} E _{off} E _{ts} t _{d(on)}	Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time	$R_G = 10\Omega, V_{GE} = 15V,$	 	15 30 65 50 160 200 360	 130 150 600	ns ns ns ns uJ uJ
Switchin td(on) tr td(off) tf Eon Eoff Ets td(on) tr	Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time	$R_G = 10\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 25^{\circ}C$	 	15 30 65 50 160 200 360 30	 130 150 600	ns ns ns ns uJ uJ uJ
Switchin td(on) tr td(off) tf Eon Eoff Ets td(on) tr td(off)	Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time	$R_{G}=10\Omega,\ V_{GE}=15V,$ Inductive Load, $T_{C}=25^{\circ}C$ $V_{CC}=300\ V,\ I_{C}=20A,$ $R_{G}=10\Omega,\ V_{GE}=15V,$	 	15 30 65 50 160 200 360 30 37	 130 150 600	ns ns ns ns uJ uJ uJ
Switchin td(on) tr td(off) tf Eon Eoff Ets td(on) tr td(off)	Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-Off Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time	$R_G = 10\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 25^{\circ}C$	 	15 30 65 50 160 200 360 30 37 110	 130 150 600 200	ns ns ns ns uJ uJ uJ ns ns
Switchir td(on) tr td(off) tf Eon Eoff Ets td(on) tr td(off) tr	Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-Off Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time	$R_{G}=10\Omega,\ V_{GE}=15V,$ Inductive Load, $T_{C}=25^{\circ}C$ $V_{CC}=300\ V,\ I_{C}=20A,$ $R_{G}=10\Omega,\ V_{GE}=15V,$	 	15 30 65 50 160 200 360 30 37 110	 130 150 600 200 250	ns ns ns ns uJ uJ uJ ns ns
Switchir t _{d(on)} t _r t _{d(off)} t _f E _{on} E _{ts} t _{d(on)} t _r t _t E _{ts} t _{d(on)} t _t t _t t _t t _{d(off)} t _t t	Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-Off Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-Off Delay Time Fall Time Turn-On Switching Loss	$R_{G}=10\Omega,\ V_{GE}=15V,$ Inductive Load, $T_{C}=25^{\circ}C$ $V_{CC}=300\ V,\ I_{C}=20A,$ $R_{G}=10\Omega,\ V_{GE}=15V,$	 	15 30 65 50 160 200 360 37 110 144 310	 130 150 600 200 250	ns ns ns ns uJ uJ uJ ns ns ns
Switchin t _{d(on)} t _r t _{d(off)} t _f E _{on} E _{off} Ets t _{d(on)} t _r t _{d(off)} t _f E _{on} E _{off} E _{ts}	Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-Off Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-Off Switching Loss Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-On Switching Loss	$\begin{split} R_G &= 10\Omega, \ V_{GE} = 15 \text{V}, \\ \text{Inductive Load, } T_C = 25^{\circ}\text{C} \end{split}$ $V_{CC} &= 300 \ \text{V}, \ I_C = 20 \text{A}, \\ R_G &= 10\Omega, \ V_{GE} = 15 \text{V}, \\ \text{Inductive Load, } T_C = 125^{\circ}\text{C} \end{split}$		15 30 65 50 160 200 360 30 37 110 144 310 430	 130 150 600 200 250	ns ns ns uJ uJ ns ns ns ns uJ
Switchin t _{d(on)} t _r t _{d(off)} t _f E _{on} E _{off} E _{ts} t _{d(on)} t _r t _t E _{on} E _{ts} C _g E _{th}	Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-Off Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-Off Switching Loss Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Turn-Off Switching Loss	$\begin{aligned} &R_G=10\Omega,V_{GE}=15\text{V},\\ &\text{Inductive Load,}T_C=25^\circ\text{C} \end{aligned}$ $\begin{aligned} &V_{CC}=300\text{V},I_C=20\text{A},\\ &R_G=10\Omega,V_{GE}=15\text{V},\\ &\text{Inductive Load,}T_C=125^\circ\text{C} \end{aligned}$ $\begin{aligned} &V_{CE}=300\text{V},I_C=20\text{A},\end{aligned}$		15 30 65 50 160 200 360 30 37 110 144 310 430 740	 130 150 600 200 250 1200	ns ns ns uJ uJ ns ns ns ns uJ
$\begin{array}{c} \textbf{Switchii} \\ \textbf{t}_{d(on)} \\ \textbf{t}_{r} \\ \textbf{t}_{d(off)} \\ \textbf{t}_{f} \\ \textbf{E}_{on} \\ \textbf{E}_{off} \end{array}$	Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-Off Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Total Switching Loss Total Switching Loss Total Gate Charge	$\begin{split} R_G &= 10\Omega, \ V_{GE} = 15 \text{V}, \\ \text{Inductive Load, } T_C = 25^{\circ}\text{C} \end{split}$ $V_{CC} &= 300 \ \text{V}, \ I_C = 20 \text{A}, \\ R_G &= 10\Omega, \ V_{GE} = 15 \text{V}, \\ \text{Inductive Load, } T_C = 125^{\circ}\text{C} \end{split}$		15 30 65 50 160 200 360 30 37 110 144 310 430 740	 130 150 600 200 250 1200 150	ns ns ns uJ uJ ns ns ns uJ uJ ns ns ns uJ uJ uJ uJ uJ uJ uJ uJ uJ nC

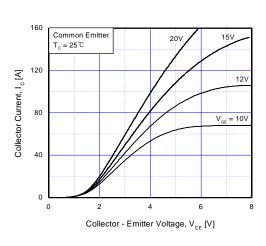


Fig 1. Typical Output Characteristics

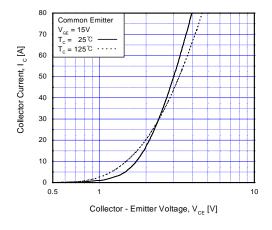


Fig 2. Typical Saturation Voltage Characteristics

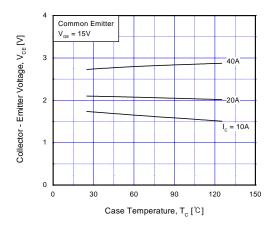


Fig 3. Saturation Voltage vs. Case
Temperature at Variant Current Level

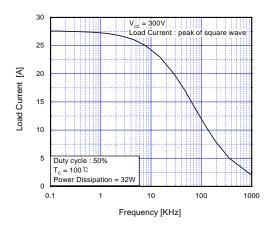


Fig 4. Load Current vs. Frequency

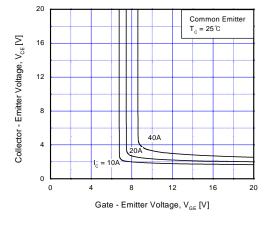


Fig 5. Saturation Voltage vs. V_{GE}

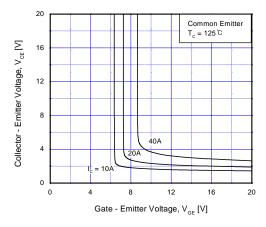
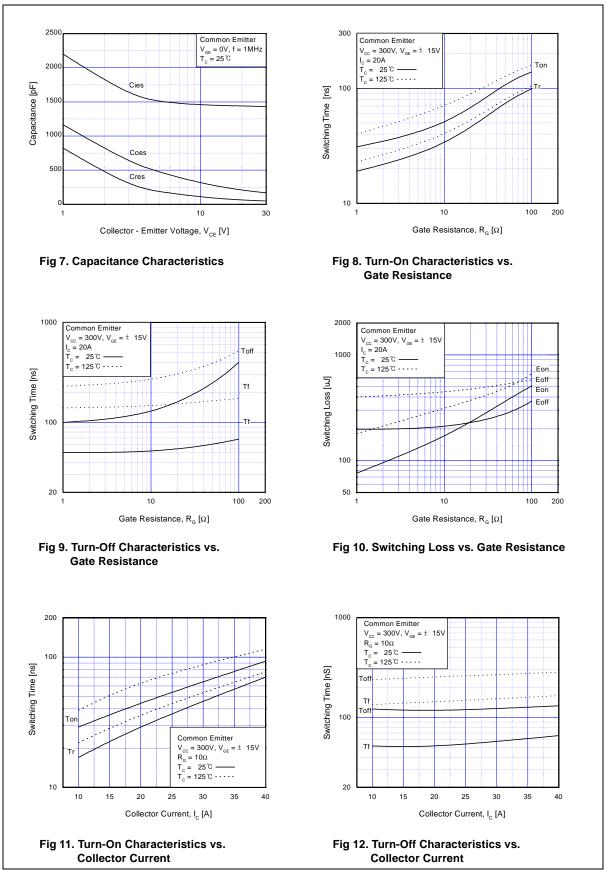
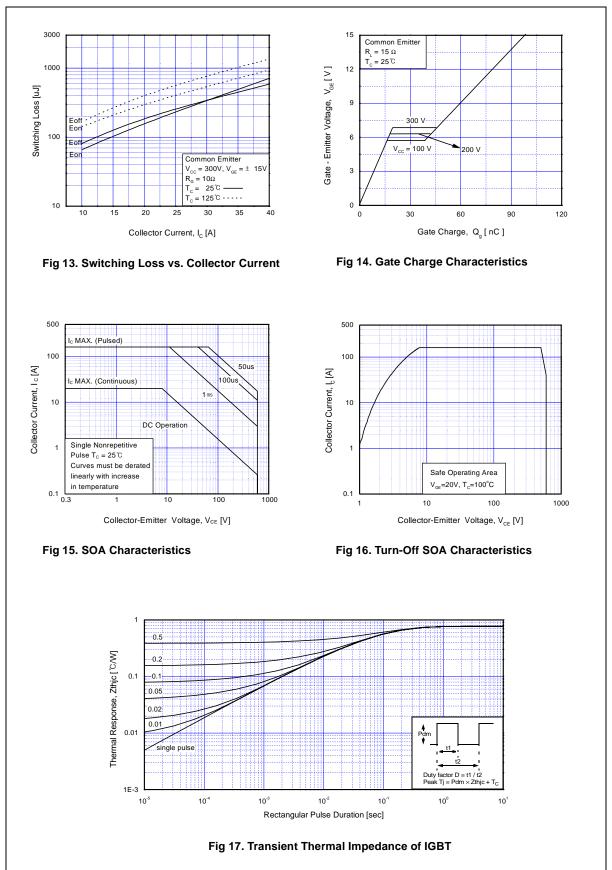


Fig 6. Saturation Voltage vs. $V_{\rm GE}$

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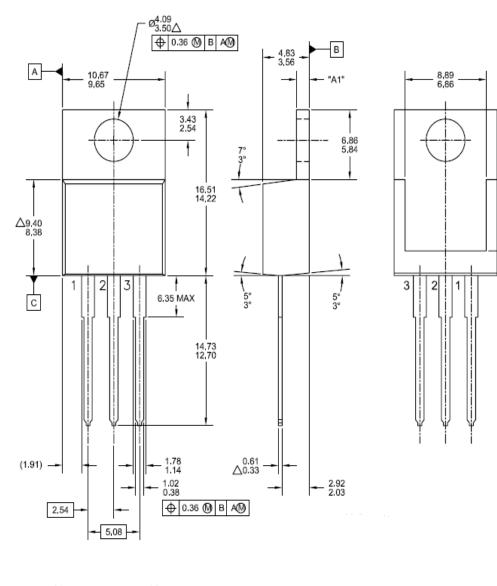
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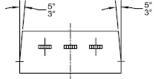


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Mechanical Dimensions

TO - 220





Dimensions in Millimeters

△13,40 12.19

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